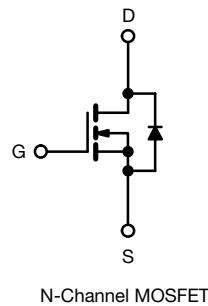
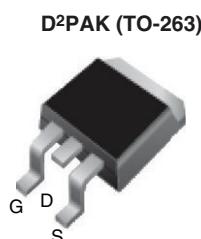


Power MOSFET

PRODUCT SUMMARY		
V _{DS} (V)	600	
R _{DS(on)} (Ω)	V _{GS} = 10 V	0.75
Q _g max. (nC)	49	
Q _{gs} (nC)	13	
Q _{gd} (nC)	20	
Configuration	Single	



ORDERING INFORMATION

Package	D ² PAK (TO-263)	D ² PAK (TO-263)	D ² PAK (TO-263)
Lead (Pb)-free and Halogen-free	SiHFS9N60A-GE3	SiHFS9N60ATRR-GE3 ^a	SiHFS9N60ATRL-GE3 ^a
Lead (Pb)-free	IRFS9N60APbF	IRFS9N60ATRRPbF ^a	IRFS9N60ATRLPbF ^a
	SiHFS9N60A-E3	SiHFS9N60ATR-E3 ^a	SiHFS9N60ATL-E3 ^a

Note

a. See device orientation.

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V _{DS}	600	V
Gate-Source Voltage	V _{GS}	± 30	
Continuous Drain Current	I _D	9.2	A
		5.8	
Pulsed Drain Current ^a	I _{DM}	37	
Linear Derating Factor		1.3	W/°C
Single Pulse Avalanche Energy ^b	E _{AS}	290	mJ
Repetitive Avalanche Current ^a	I _{AR}	9.2	A
Repetitive Avalanche Energy ^a	E _{AR}	17	mJ
Maximum Power Dissipation	P _D	170	W
Peak Diode Recovery dV/dt ^c	dV/dt	5.0	V/ns
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C
Soldering Recommendations (Peak temperature) ^d	for 10 s	300	

Notes

a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).

b. Starting T_J = 25 °C, L = 6.8 mH, R_g = 25 Ω, I_{AS} = 9.2 A (see fig. 12).

c. I_{SD} ≤ 9.2 A, dI/dt ≤ 50 A/μs, V_{DD} ≤ V_{DS}, T_J ≤ 150 °C.

d. 1.6 mm from case.


RoHS*

Available


HALOGEN FREE

Available

THERMAL RESISTANCE RATINGS

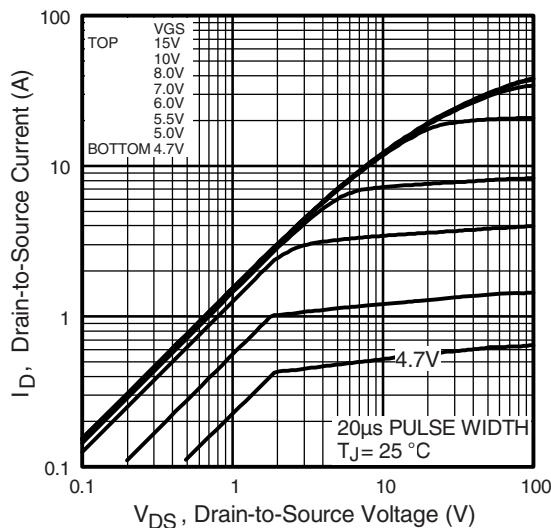
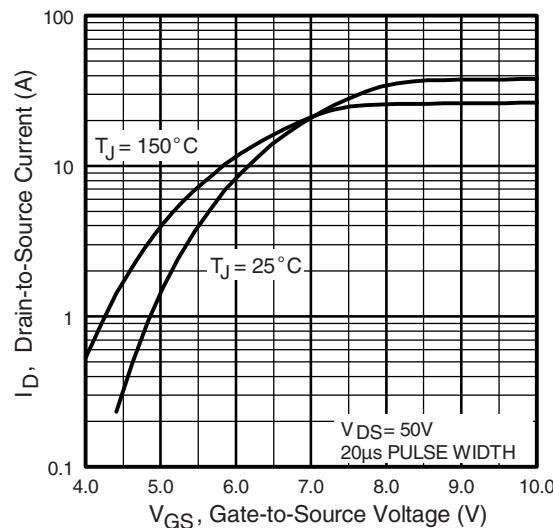
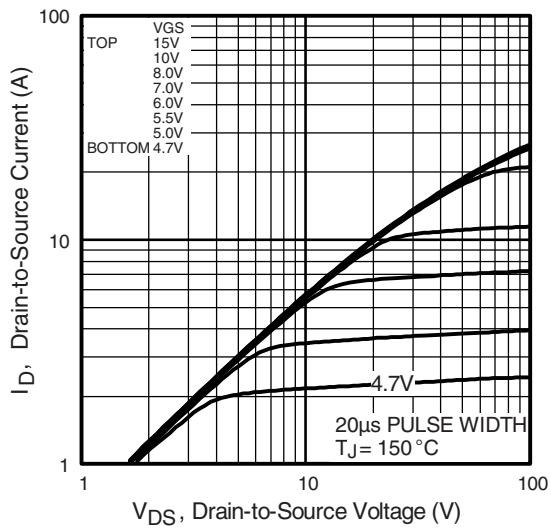
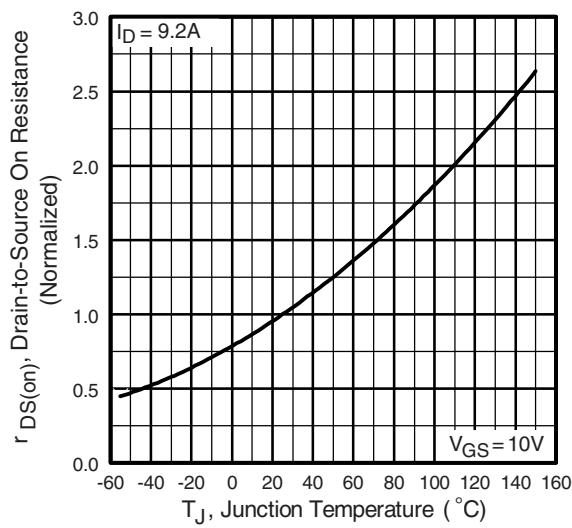
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	40	
Maximum Junction-to-Case (Drain)	R_{thJC}	-	0.75	°C/W

SPECIFICATIONS ($T_J = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0$, $I_D = 250$ μA		600	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to 25 °C, $I_D = 1$ mA		-	0.66	-	V/°C
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250$ μA		2.0	-	4.0	V
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 30$ V		-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 600$ V, $V_{GS} = 0$ V		-	-	25	μA
		$V_{DS} = 480$ V, $V_{GS} = 0$ V, $T_J = 125$ °C		-	-	250	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10$ V	$I_D = 5.5$ A ^b	-	-	0.75	Ω
Forward Transconductance	g_{fs}	$V_{DS} = 25$ V, $I_D = 3.1$ A		5.5	-	-	S
Dynamic							
Input Capacitance	C_{iss}	$V_{GS} = 0$ V, $V_{DS} = 25$ V, $f = 1.0$ MHz, see fig. 5		-	1400	-	pF
Output Capacitance	C_{oss}			-	180	-	
Reverse Transfer Capacitance	C_{rss}			-	7.1	-	
Output Capacitance	C_{oss}	$V_{GS} = 0$ V	$V_{DS} = 1.0$ V, $f = 1.0$ MHz	-	1957	-	pF
			$V_{DS} = 480$ V, $f = 1.0$ MHz	-	49	-	
			$V_{DS} = 0$ V to 480 V ^c	-	96	-	
Total Gate Charge	Q_g	$V_{GS} = 10$ V	$I_D = 9.2$ A, $V_{DS} = 400$ V see fig. 6 and 13 ^b	-	-	49	nC
Gate-Source Charge	Q_{gs}			-	-	13	
Gate-Drain Charge	Q_{gd}			-	-	20	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 300$ V, $I_D = 9.2$ A $R_g = 9.1$ Ω, $R_D = 35.5$ Ω, see fig. 10 ^b		-	13	-	ns
Rise Time	t_r			-	25	-	
Turn-Off Delay Time	$t_{d(off)}$			-	30	-	
Fall Time	t_f			-	22	-	
Gate Input Resistance	R_g		$f = 1$ MHz, open drain	0.5	-	3.2	Ω
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode		-	-	9.2	A
Pulsed Diode Forward Current ^a	I_{SM}			-	-	37	
Body Diode Voltage	V_{SD}	$T_J = 25$ °C, $I_S = 9.2$ A, $V_{GS} = 0$ V ^b		-	-	1.5	V
Body Diode Reverse Recovery Time	t_{rr}	$T_J = 25$ °C, $I_F = 9.2$ A, $dI/dt = 100$ A/μs ^b		-	530	800	ns
Body Diode Reverse Recovery Charge	Q_{rr}			-	3.0	4.4	μC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)					

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- Pulse width ≤ 300 μs; duty cycle ≤ 2 %.
- C_{oss} eff. is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80 % V_{DS} .

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Fig. 1 - Typical Output Characteristics

Fig. 3 - Typical Transfer Characteristics

Fig. 2 - Typical Output Characteristics

Fig. 4 - Normalized On-Resistance vs. Temperature

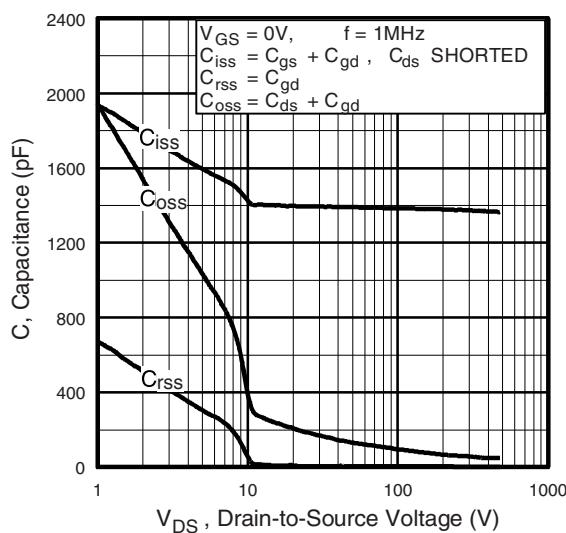


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

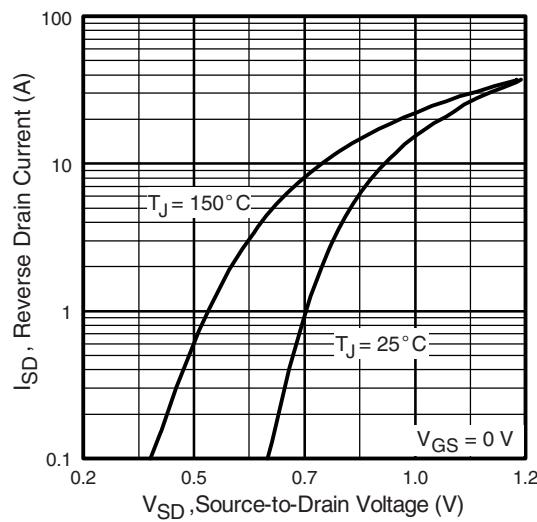


Fig. 7 - Typical Source-Drain Diode Forward Voltage

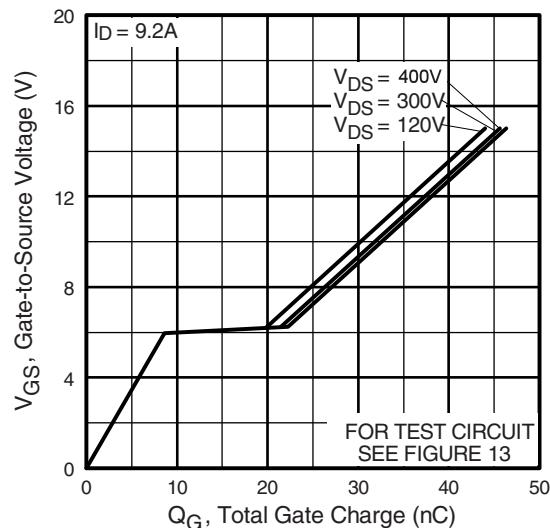


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

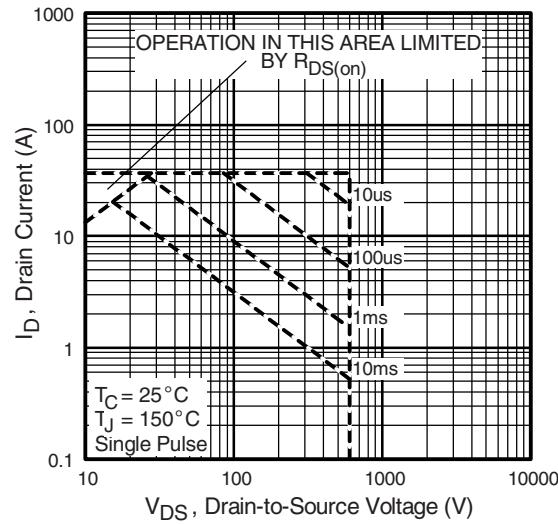
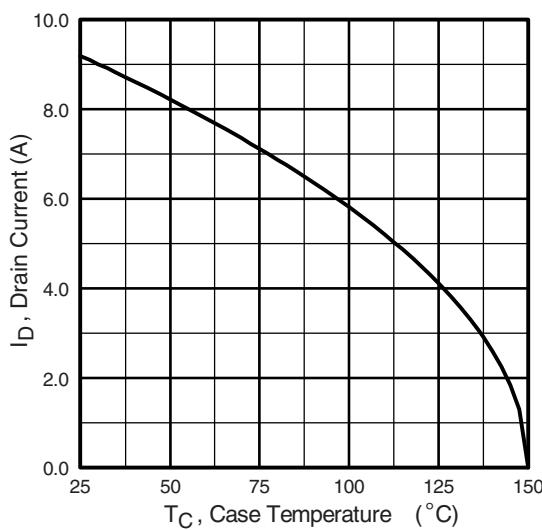
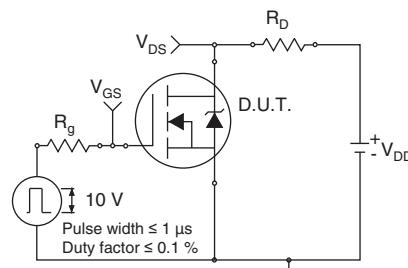
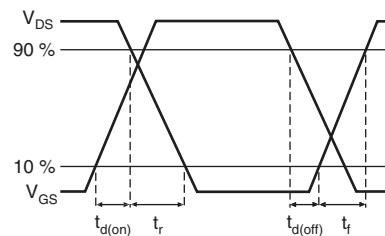
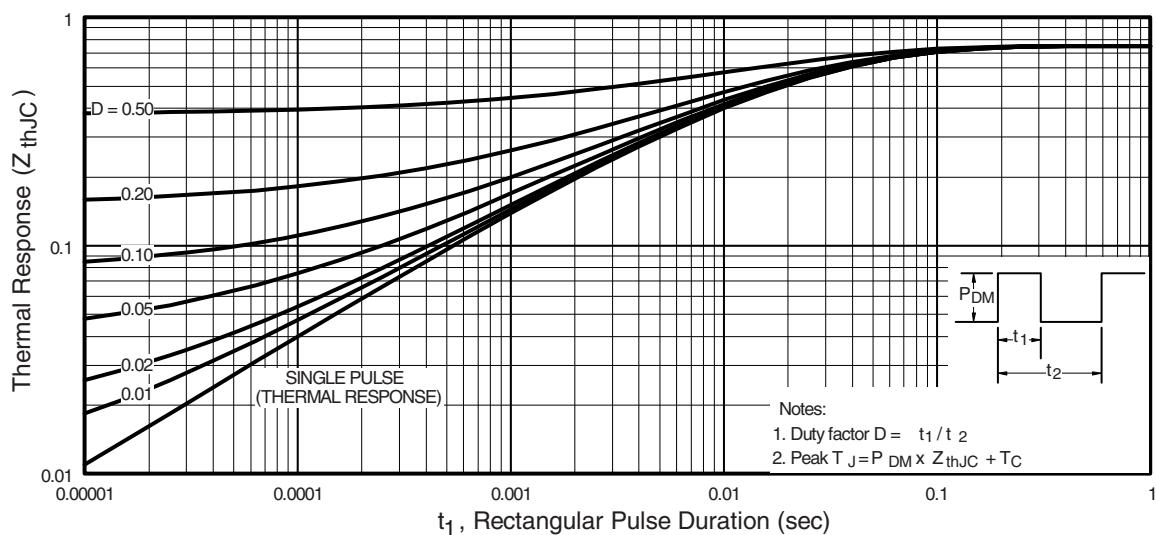
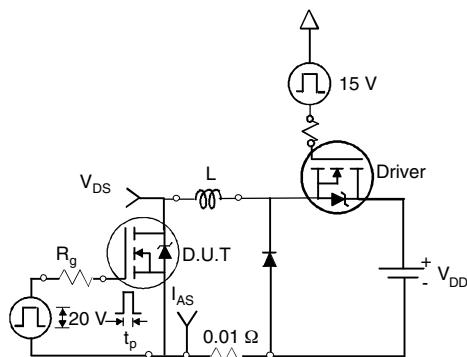
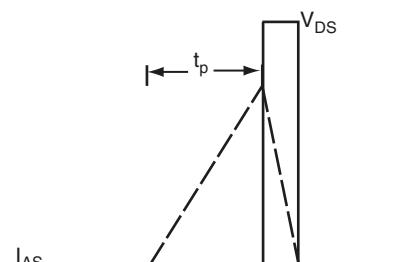


Fig. 1 - Maximum Safe Operating Area


Fig. 8 - Maximum Drain Current vs. Case Temperature

Fig. 10a - Switching Time Test Circuit

Fig. 10b - Switching Time Waveforms

Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

Fig. 12a - Unclamped Inductive Test Circuit

Fig. 12b - Unclamped Inductive Waveforms

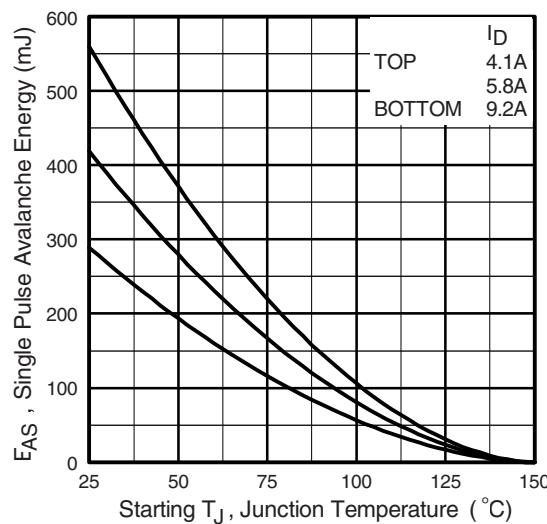


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

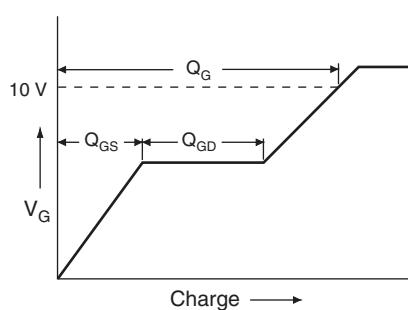


Fig. 13a - Basic Gate Charge Waveform

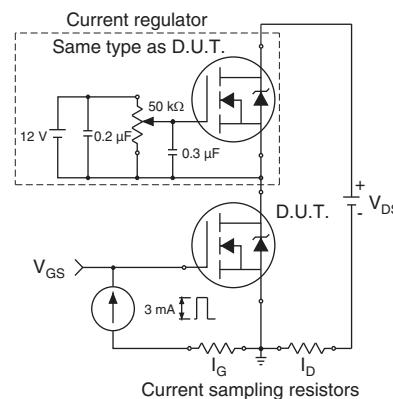


Fig. 13b - Gate Charge Test Circuit

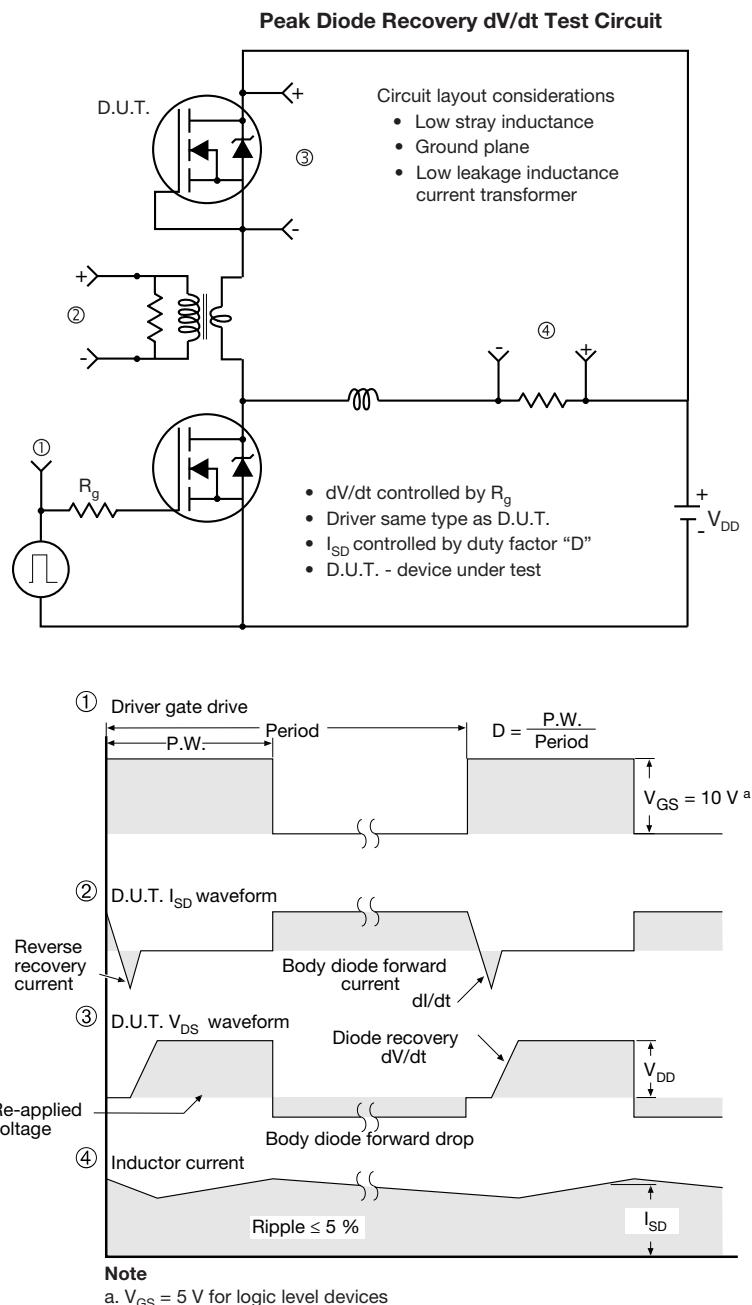
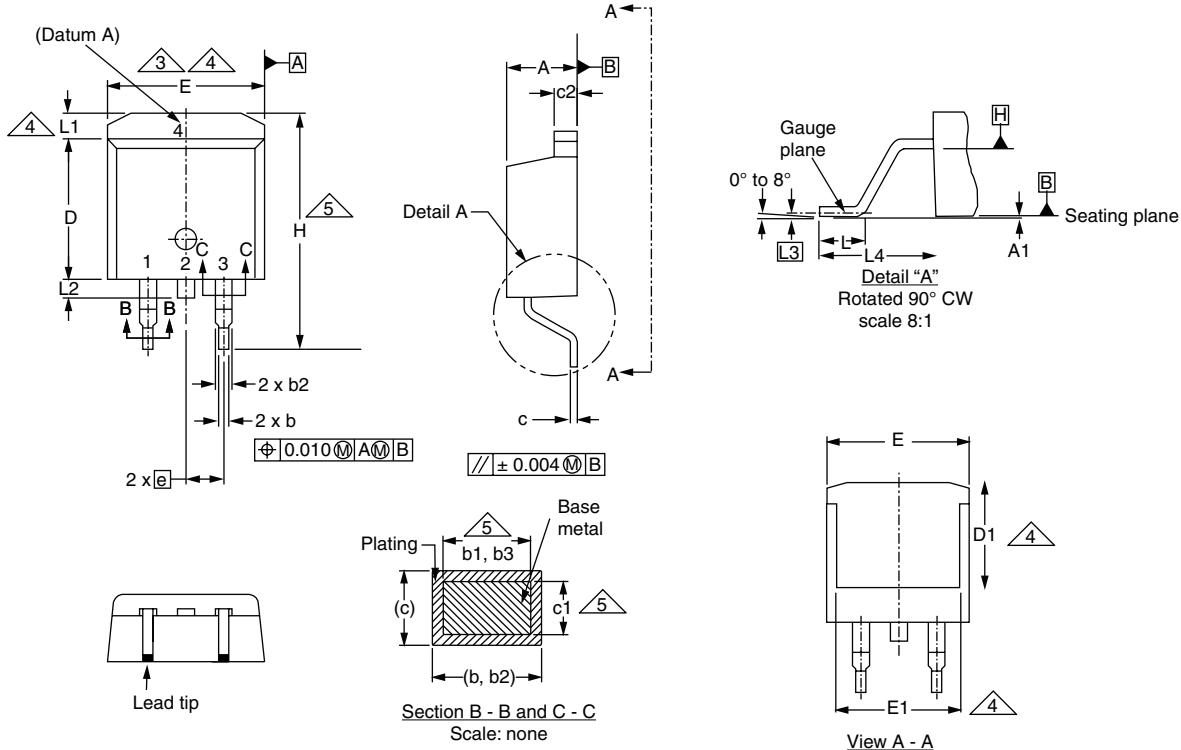


Fig. 14 - For N-Channel

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TO-263AB (HIGH VOLTAGE)



	MILLIMETERS		INCHES	
DIM.	MIN.	MAX.	MIN.	MAX.
A	4.06	4.83	0.160	0.190
A1	0.00	0.25	0.000	0.010
b	0.51	0.99	0.020	0.039
b1	0.51	0.89	0.020	0.035
b2	1.14	1.78	0.045	0.070
b3	1.14	1.73	0.045	0.068
c	0.38	0.74	0.015	0.029
c1	0.38	0.58	0.015	0.023
c2	1.14	1.65	0.045	0.065
D	8.38	9.65	0.330	0.380

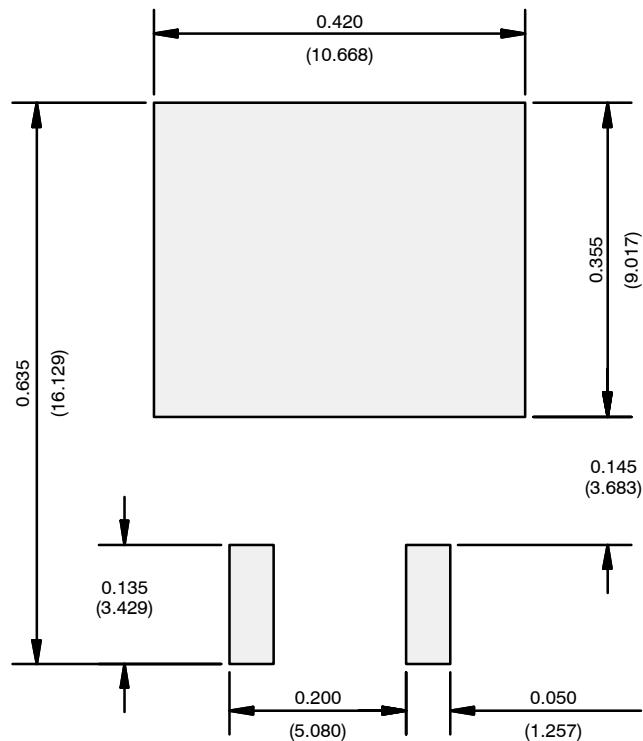
	MILLIMETERS		INCHES	
DIM.	MIN.	MAX.	MIN.	MAX.
D1	6.86	-	0.270	-
E	9.65	10.67	0.380	0.420
E1	6.22	-	0.245	-
e	2.54 BSC		0.100 BSC	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	-	1.65	-	0.066
L2	-	1.78	-	0.070
L3	0.25 BSC		0.010 BSC	

ECN: S-82110-Rev. A, 15-Sep-08

DW

Notes

1. Dimensioning and tolerancing per ASME Y14.5M-1994.
2. Dimensions are shown in millimeters (inches).
3. Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body at datum A.
4. Thermal PAD contour optional within dimension E, L1, D1 and E1.
5. Dimension b1 and c1 apply to base metal only.
6. Datum A and B to be determined at datum plane H.
7. Outline conforms to JEDEC outline TO-263AB

RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead

Recommended Minimum Pads
Dimensions in Inches/(mm)

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